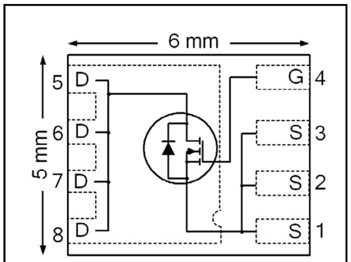
International
IOR Rectifier

Fast/RFET™
IRFH4226PbF

HEXFET® Power MOSFET

V_{DSS}	25	V
$R_{DS(on)}$ max (@ V_{GS} = 10V)	2.4	mΩ
(@ V_{GS} = 4.5V)	3.3	
Qg (typical)	16	nC
I_D (@$T_{C\ (Bottom)}$ = 25°C)	70⑥⑦	A



PQFN 5X6 mm

Applications

- Control MOSFET for Sync Buck Converters
- Secondary Synchronous Rectifier MOSFET for isolated DC-DC converters

Features		Benefits
Low Charge (typical 16 nC)		Low Switching Losses
Low R_{DSon} (<2.4 mΩ)		Lower Conduction Losses
Low Thermal Resistance to PCB (<2.7 °C/W)		Enable better Thermal Dissipation
Low Profile (<0.9 mm)	results in	Increased Power Density
Industry-Standard Pinout	⇒	Multi-Vendor Compatibility
Compatible with Existing Surface Mount Techniques		Easier Manufacturing
RoHS Compliant, Halogen-Free		Environmentally Friendlier
MSL1, Industrial Qualification		Increased Reliability

Base part number	Package Type	Standard Pack		Orderable Part Number
		Form	Quantity	
IRFH4226PbF	PQFN 5mm x 6 mm	Tape and Reel	4000	IRFH4226TRPbF

Absolute Maximum Ratings

	Parameter	Max.	Units
V_{GS}	Gate-to-Source Voltage	± 20	V
I_D @ T_A = 25°C	Continuous Drain Current, V_{GS} @ 10V	30	A
I_D @ $T_{C(Bottom)}$ = 25°C	Continuous Drain Current, V_{GS} @ 10V	110⑥⑦	
I_D @ $T_{C(Bottom)}$ = 100°C	Continuous Drain Current, V_{GS} @ 10V	69	
I_D @ T_C = 25°C	Continuous Drain Current, V_{GS} @ 10V (Source Bonding Technology Limited)	70⑥⑦	
I_{DM}	Pulsed Drain Current ①	460⑧	
P_D @T_A = 25°C	Power Dissipation ⑤	3.4	W
P_D @$T_{C(Bottom)}$ = 25°C	Power Dissipation ⑤	46	
	Linear Derating Factor ⑤	0.027	W/°C
T_J T_{STG}	Operating Junction and Storage Temperature Range	-55 to + 150	°C

Notes ① through ⑧ are on page 8

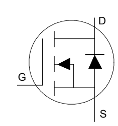
Static @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
BV_{DSS}	Drain-to-Source Breakdown Voltage	25	——	——	V	V_{GS} = 0V, I_D = 250μA
$\Delta BV_{DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	——	21	——	mV/°C	Reference to 25°C, I_D = 1mA
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	——	1.7	2.4	mΩ	V_{GS} = 10V, I_D = 30A ③
		——	2.6	3.3		V_{GS} = 4.5V, I_D = 30A ③
$V_{GS(th)}$	Gate Threshold Voltage	1.1	1.6	2.1	V	V_{DS} = V_{GS}, I_D = 50μA
$\Delta V_{GS(th)}$	Gate Threshold Voltage Coefficient	——	-5.7	——	mV/°C	
I_{DSS}	Drain-to-Source Leakage Current	——	——	1.0	μA	V_{DS} = 20V, V_{GS} = 0V
I_{GSS}	Gate-to-Source Forward Leakage	——	——	100	nA	V_{GS} = 20V
	Gate-to-Source Reverse Leakage	——	——	-100		V_{GS} = -20V
gfs	Forward Transconductance	136	——	——	S	V_{DS} = 10V, I_D = 30A
Q_g	Total Gate Charge	——	32	——	nC	V_{GS} = 10V, V_{DS} = 13V, I_D = 30A
Q_g	Total Gate Charge	——	16	24	nC	V_{DS} = 13V
Q_{gs1}	Pre-Vth Gate-to-Source Charge	——	3.6	——		V_{GS} = 4.5V
Q_{gs2}	Post-Vth Gate-to-Source Charge	——	2.0	——		I_D = 30A
Q_{gd}	Gate-to-Drain Charge	——	5.8	——		
Q_{godr}	Gate Charge Overdrive	——	4.6	——		
Q_{sw}	Switch Charge (Q_{gs2} + Q_{gd})	——	7.8	——		
Q_{oss}	Output Charge	——	15	——	nC	V_{DS} = 16V, V_{GS} = 0V
R_G	Gate Resistance	——	1.1	——	Ω	
$t_{d(on)}$	Turn-On Delay Time	——	11	——	ns	V_{DD} = 13V, V_{GS} = 4.5V
t_r	Rise Time	——	35	——		I_D = 30A
$t_{d(off)}$	Turn-Off Delay Time	——	14	——		R_G=1.8Ω
t_f	Fall Time	——	8.1	——		
C_{iss}	Input Capacitance	——	2000	——	pF	V_{GS} = 0V
C_{oss}	Output Capacitance	——	570	——		V_{DS} = 13V
C_{rss}	Reverse Transfer Capacitance	——	150	——		f = 1.0MHz

Avalanche Characteristics

	Parameter	Max.	Units.
E_{AS}	Single Pulse Avalanche Energy ②	131	**mJ**
I_{AR}	Avalanche Current ①	30	**A**

Diode Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	——	——	70⑥⑦	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I_{SM}	Pulsed Source Current (Body Diode) ①	——	——	460⑧		
V_{SD}	Diode Forward Voltage	——	——	1.0	V	T_J = 25°C, I_S = 30A, V_{GS} = 0V ③
t_{rr}	Reverse Recovery Time	——	16	24	ns	T_J = 25°C, I_F = 30A, V_{DD} = 13V
Q_{rr}	Reverse Recovery Charge	——	28	42	nC	di/dt = 450A/μs ③

Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JC}$ (Bottom)	Junction-to-Case ④	——	2.7	°C/W
$R_{\theta JC}$ (Top)	Junction-to-Case ④	——	27	
$R_{\theta JA}$	Junction-to-Ambient ⑤	——	37	
$R_{\theta JA}$ (<10s)	Junction-to-Ambient ⑤	——	23	

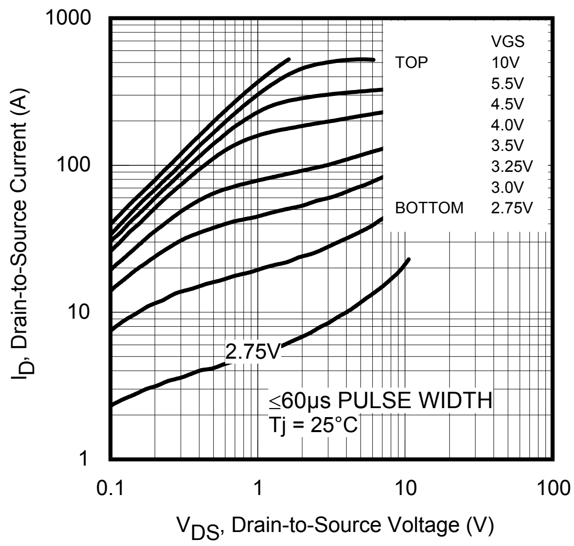


Fig 1. Typical Output Characteristics

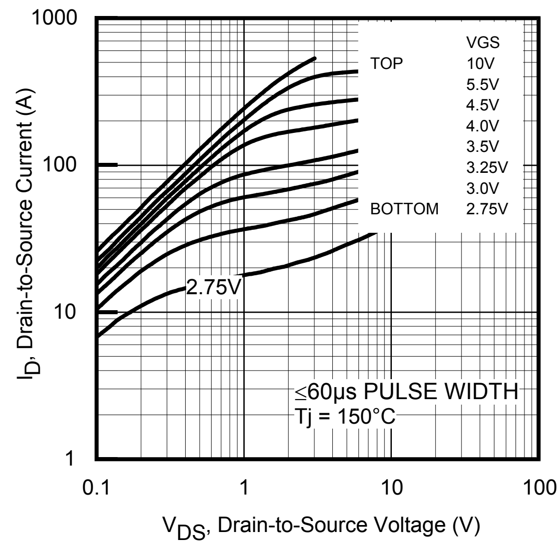


Fig 2. Typical Output Characteristics

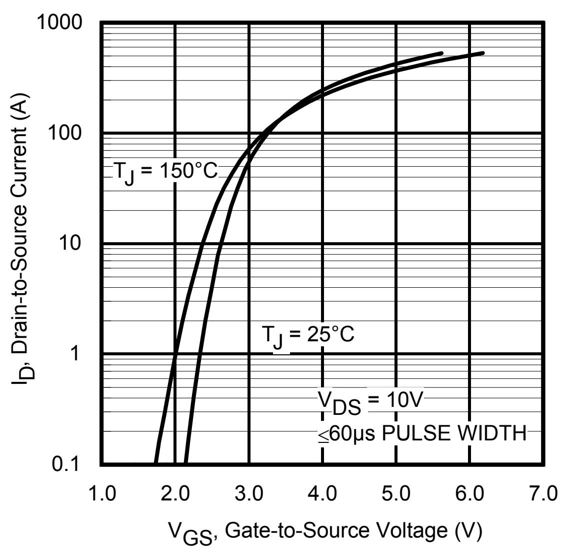


Fig 3. Typical Transfer Characteristics

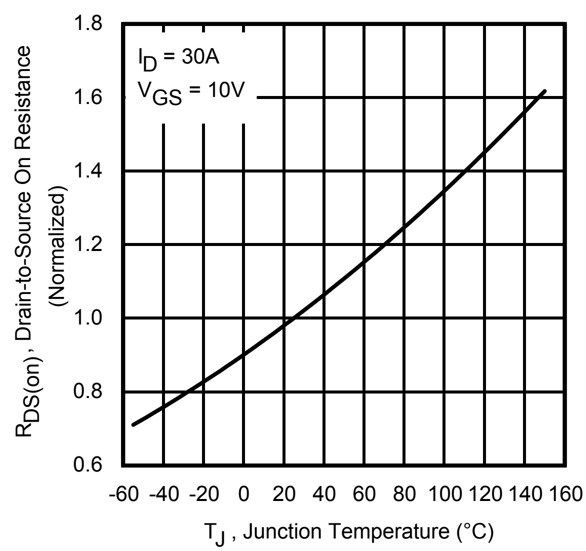


Fig 4. Normalized On-Resistance vs. Temperature

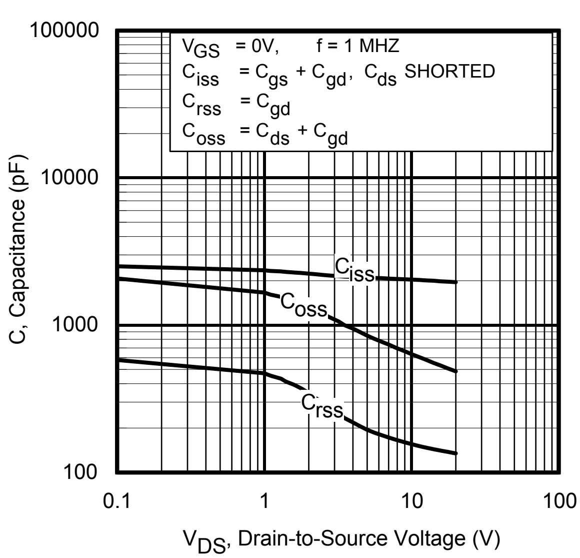


Fig 5. Typical Capacitance vs. Drain-to-Source Voltage

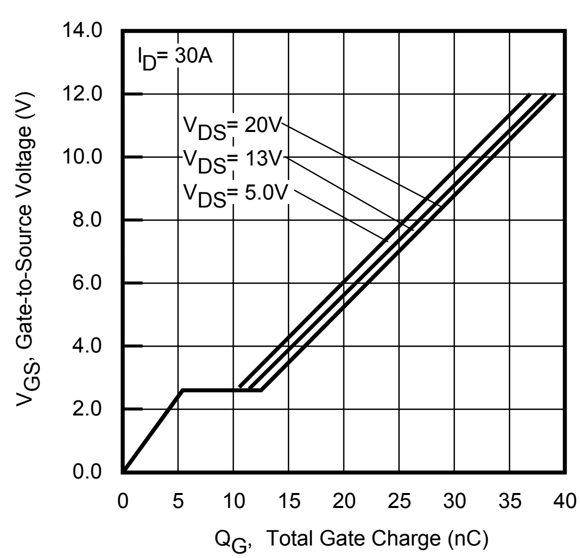


Fig 6. Typical Gate Charge vs. Gate-to-Source Voltage

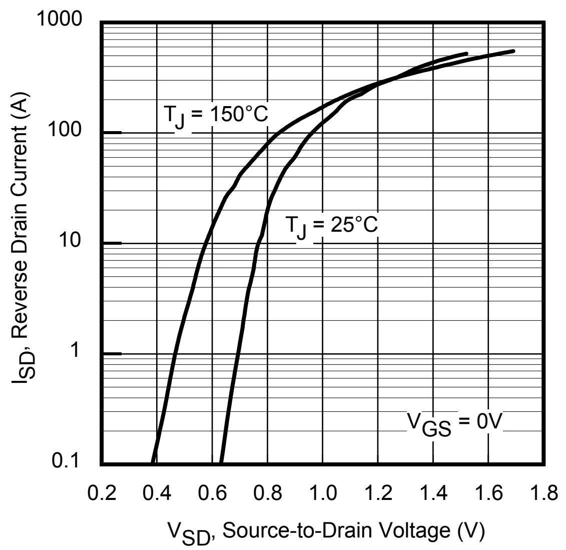


Fig 7. Typical Source-Drain Diode Forward Voltage

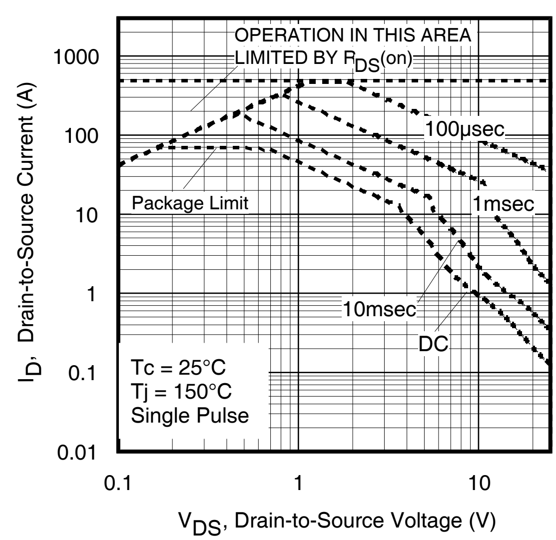


Fig 8. Maximum Safe Operating Area

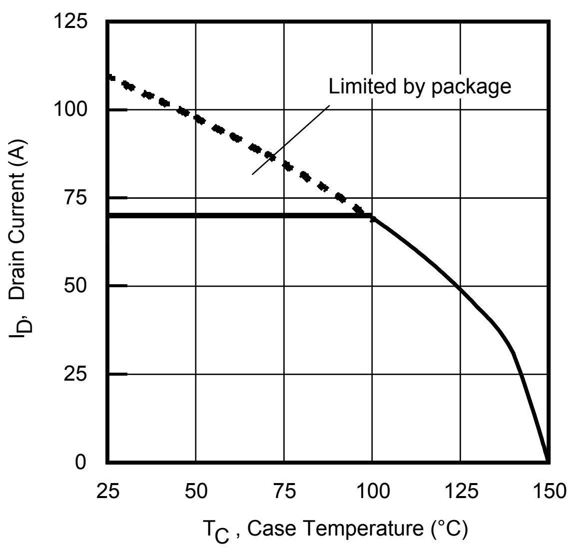


Fig 9. Maximum Drain Current vs. Case Temperature

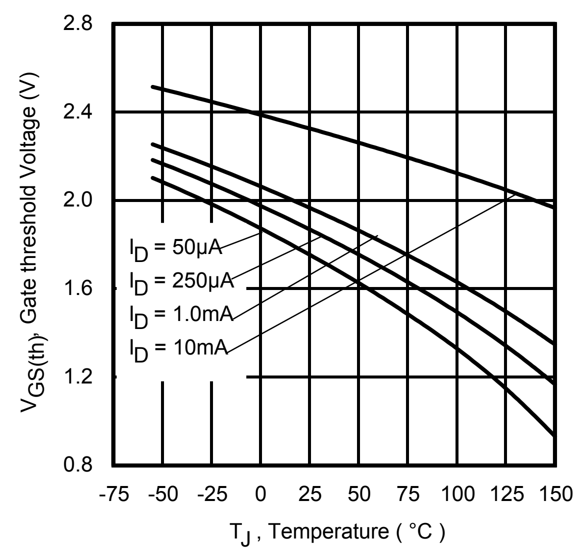


Fig 10. Threshold Voltage Vs. Temperature

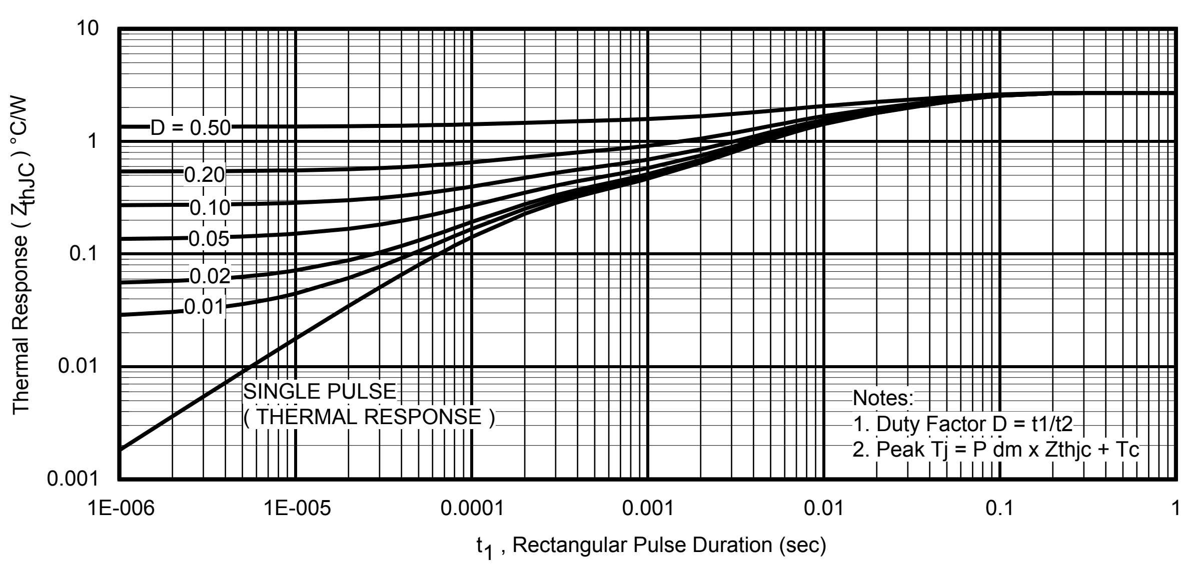


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

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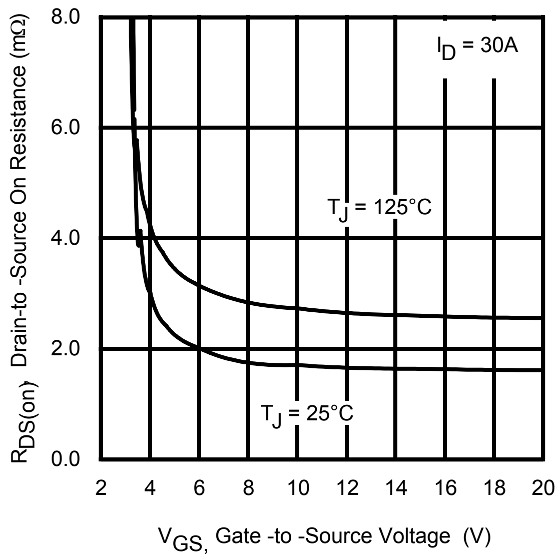


Fig 12. On– Resistance vs. Gate Voltage

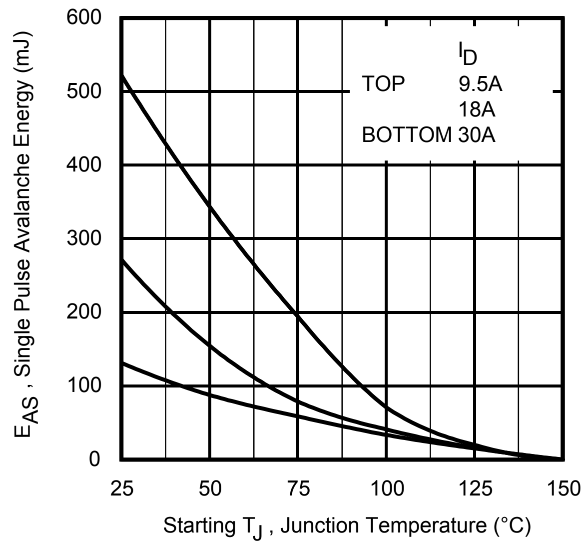


Fig 13. Maximum Avalanche Energy vs. Drain Current

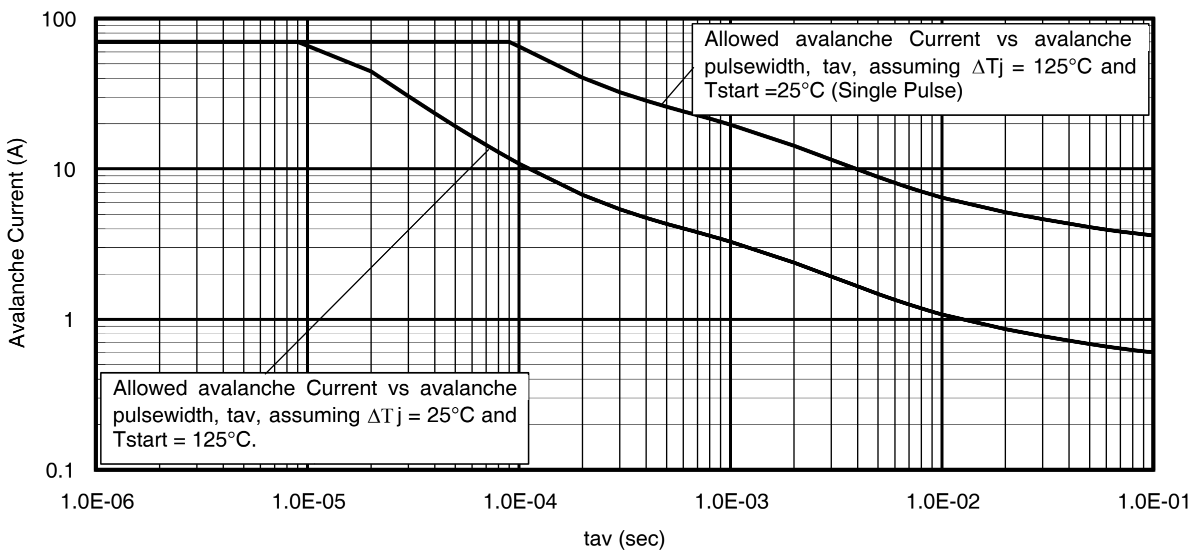


Fig 14. Single Avalanche Current vs. pulse Width

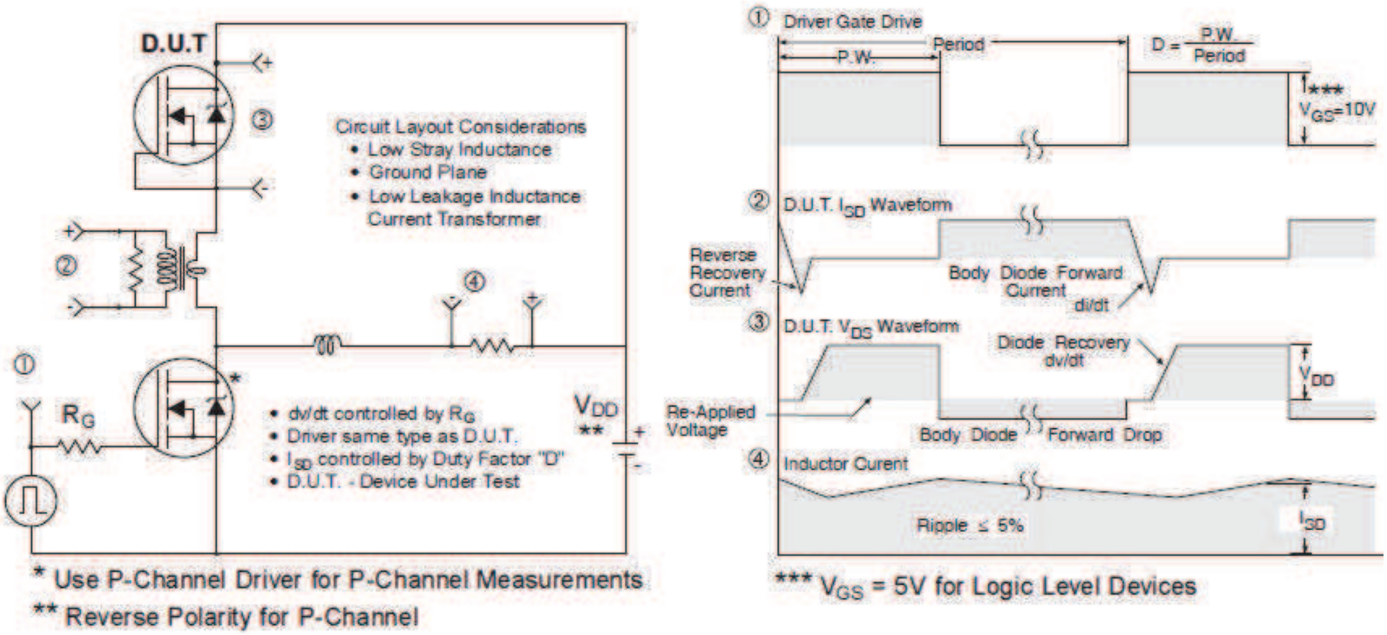


Fig 15. Peak Diode Recovery dv/dt Test Circuit for N-Channel HEXFET® Power MOSFETs

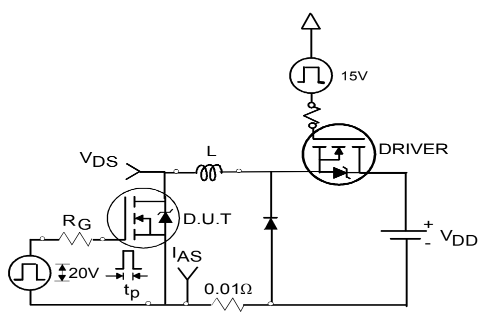


Fig 16a. Unclamped Inductive Test Circuit

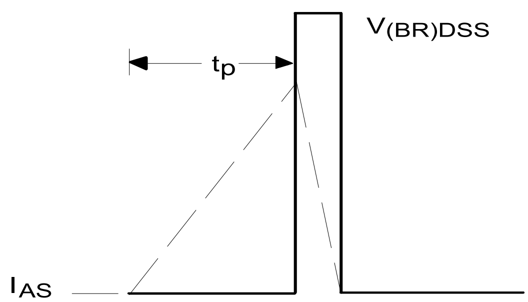


Fig 16b. Unclamped Inductive Waveforms

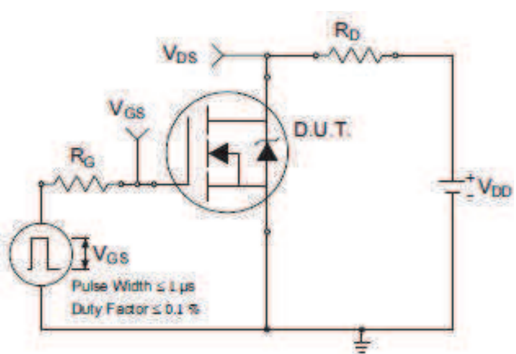


Fig 17a. Switching Time Test Circuit

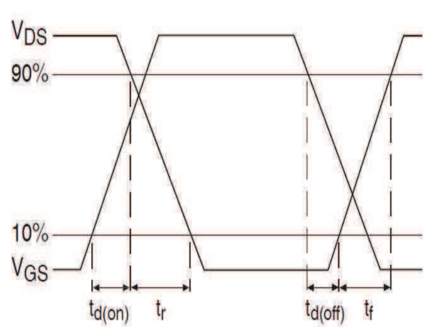


Fig 17b. Switching Time Waveforms

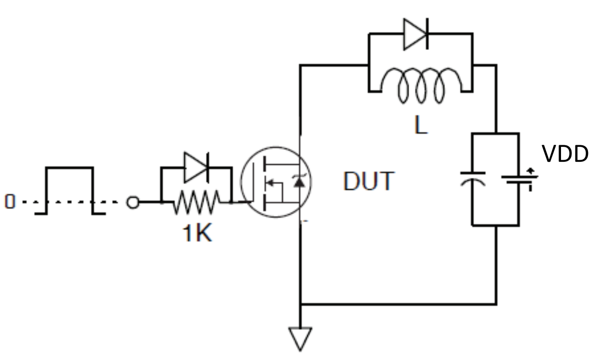


Fig 18. Gate Charge Test Circuit

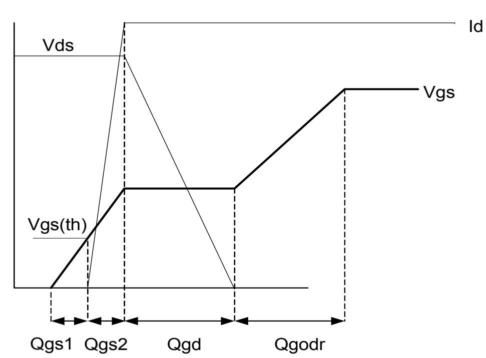
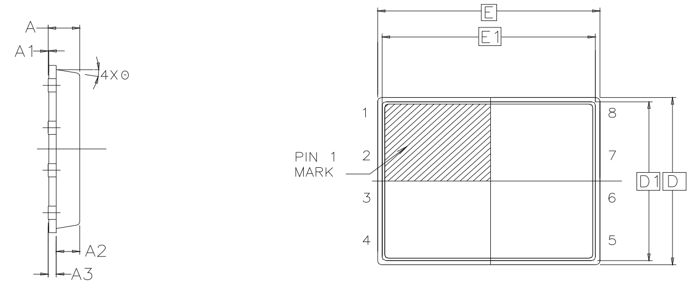


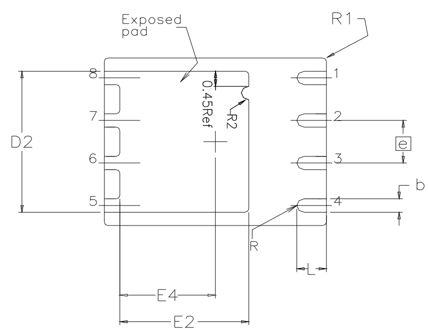
Fig 19. Gate Charge Waveform

PQFN 5x6 Outline "B" Package Details



SIDE VIEW   TOP VIEW

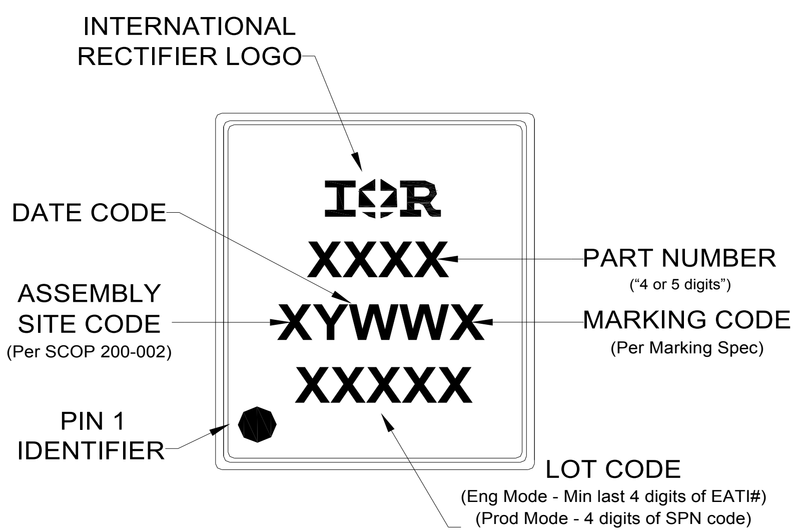
SYMBOL \ DIM	MIN	NOM	MAX
A	0.800	0.830	1.05
A1	0.000	0.020	0.050
A2	0.580	0.630	0.680
A3	0.254 REF		
Θ	0°	10°	12°
b	0.350	0.400	0.470
D	4.850	5.000	5.150
D1	4.675	4.750	5.000
D2	3.700	4.210	4.300
e	1.270 BSC		
E	5.850	6.000	6.150
E1	5.675	5.750	6.000
E2	3.380	3.480	3.760
E4	2.480	2.580	2.680
L	0.550	0.800	0.900
R	0.200 REF		
R1	0.100 REF		
R2	0.150	0.200	0.250



BOTTOM VIEW

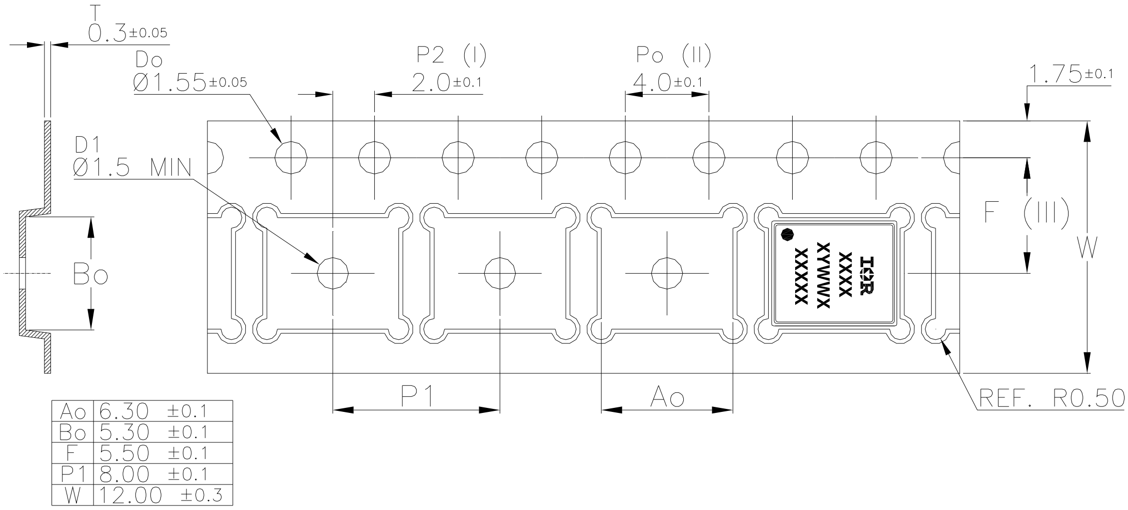
For more information on board mounting, including footprint and stencil recommendation, please refer to application note AN-1136: http://www.irf.com/technical-info/appnotes/an-1136.pdf
For more information on package inspection techniques, please refer to application note AN-1154: http://www.irf.com/technical-info/appnotes/an-1154.pdf

PQFN 5x6 Outline "B" Part Marking



Note: For the most current drawing please refer to IR website at http://www.irf.com/package/

PQFN 5x6 Outline "B" Tape and Reel



Note: For the most current drawing please refer to IR website at http://www.irf.com/package/

Qualification Information†

Qualification Level		Industrial† (per JEDEC JESD47F†† guidelines)
Moisture Sensitivity Level	PQFN 5mm x 6mm	MSL1 (per JEDEC J-STD-020D††)
RoHS Compliant	Yes	

† Qualification standards can be found at International Rectifier's web site: http://www.irf.com/product-info/reliability

†† Applicable version of JEDEC standard at the time of product release.

Notes:

① Repetitive rating; pulse width limited by max. junction temperature.
② Starting T_J = 25°C, L = 0.29mH, R_G = 50Ω, I_{AS} = 30A.
③ Pulse width ≤ 400 µs; duty cycle ≤ 2%.
④ R_θ is measured at T_J of approximately 90°C.
⑤ When mounted on 1 inch square PCB (FR-4). Please refer to AN-994 for more details: http://www.irf.com/technical-info/appnotes/an-994.pdf
⑥ Calculated continuous current based on maximum allowable junction temperature.
⑦ Current is limited to 70A by source bonding technology.
⑧ Pulse drain current is limited at 280A by source bonding technology.

International Rectifier

IR WORLD HEADQUARTERS: 101 N. Sepulveda Blvd., El Segundo, California 90245, USA

To contact International Rectifier, please visit http://www.irf.com/whoto-call/

